

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	11	(substrate near "process chamber") and (HCD or "hexachlorodisilane") and gas and silicon and hydrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 15:08
S1	3	(substrate near "process chamber") and (HCD and "hexachlorodisilane") and gas and silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 08:44
S2	24	(substrate near chamber) and (HCD or "hexachlorodisilane") and gas and silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 08:43
S3	14	(substrate near "process chamber") and (HCD or "hexachlorodisilane") and gas and silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 08:51
S4	1	(substrate near "process chamber") and (HCD or "hexachlorodisilane") and gas and silicon and hydrogen and germanium and phosphor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 08:53
S6	4	(substrate near "process chamber") and (HCD or "hexachlorodisilane") and gas and silicon and hydrogen and germanium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 08:53